## DATA S凡RET



BAV70 High-speed double diode

File under Discrete Semiconductors, SC01

## FEATURES

- Small plastic SMD package
- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 70 V
- Repetitive peak reverse voltage: max. 75 V
- Repetitive peak forward current: max. 450 mA
- Forward voltage: max. 1 V .


## APPLICATIONS

- High-speed switching in thick and thin-film circuits.


## DESCRIPTION

The BAV70 consists of two high-speed switching diodes with common cathodes, fabricated in planar technology, and encapsulated in the small plastic SMD SOT23 package.

## PINNING

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | anode (a1) |
| 2 | anode (a2) |
| 3 | common cathode |

Marking code: A4p.
Fig. 1 Simplified outline (SOT23) and symbol.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Per diode |  |  |  |  |  |
| $V_{\text {RRM }}$ | repetitive peak reverse voltage |  | - | 75 | V |
| $\mathrm{V}_{\mathrm{R}}$ | continuous reverse voltage |  | - | 70 | V |
| $\mathrm{I}_{\mathrm{F}}$ | continuous forward current | single diode loaded; see Fig.2; note 1 | - | 215 | mA |
|  |  | double diode loaded; see Fig.2; note 1 | - | 125 | mA |
| $\mathrm{I}_{\text {FRM }}$ | repetitive peak forward current |  | - | 450 | mA |
| $\mathrm{I}_{\text {FSM }}$ | non-repetitive peak forward current | $\begin{aligned} & \text { square wave; } \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C} \text { prior to } \\ & \text { surge; see Fig. } 4 \\ & \begin{array}{l} t=1 \mu \mathrm{~s} \\ t=1 \mathrm{~ms} \\ t=1 \mathrm{~s} \end{array} \end{aligned}$ | $\begin{aligned} & \text { - } \\ & \text { - } \end{aligned}$ | $\begin{aligned} & 4 \\ & 1 \\ & 0.5 \end{aligned}$ | $\begin{aligned} & \mathrm{A} \\ & \mathrm{~A} \\ & \mathrm{~A} \end{aligned}$ |
| $\mathrm{P}_{\text {tot }}$ | total power dissipation | $\mathrm{T}_{\mathrm{amb}}=25^{\circ} \mathrm{C}$; note 1 | - | 250 | mW |
| $\mathrm{T}_{\text {stg }}$ | storage temperature |  | -65 | +150 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | junction temperature |  | - | 150 | ${ }^{\circ} \mathrm{C}$ |

## Note

1. Device mounted on an FR4 printed-circuit board.

## ELECTRICAL CHARACTERISTICS

$\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: |
| Per diode |  |  |  |  |  |
| $\mathrm{V}_{\mathrm{F}}$ | forward voltage | $\begin{array}{\|l} \hline \text { see Fig. } 3 \\ \mathrm{I}_{\mathrm{F}}=1 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{F}}=50 \mathrm{~mA} \\ \mathrm{I}_{\mathrm{F}}=150 \mathrm{~mA} \\ \hline \end{array}$ |  | $\begin{gathered} 715 \\ 855 \\ 1 \\ 1.25 \end{gathered}$ | $\begin{aligned} & \mathrm{mV} \\ & \mathrm{mV} \\ & \mathrm{~V} \\ & \mathrm{~V} \end{aligned}$ |
| $\mathrm{I}_{\mathrm{R}}$ | reverse current | see Fig. 5 $\begin{aligned} & V_{R}=25 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{R}}=70 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{R}}=25 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} \\ & \mathrm{~V}_{\mathrm{R}}=70 \mathrm{~V} ; \mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C} \end{aligned}$ |  | $\begin{gathered} 30 \\ 2.5 \\ 60 \\ 100 \end{gathered}$ | nA <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ <br> $\mu \mathrm{A}$ |
| $\mathrm{C}_{\mathrm{d}}$ | diode capacitance | $\mathrm{f}=1 \mathrm{MHz} ; \mathrm{V}_{\mathrm{R}}=0$; see Fig. 6 | - | 1.5 | pF |
| $\mathrm{t}_{\mathrm{rr}}$ | reverse recovery time | when switched from $I_{F}=10 \mathrm{~mA}$ to $\mathrm{I}_{\mathrm{R}}=10 \mathrm{~mA} ; \mathrm{R}_{\mathrm{L}}=100 \Omega$; <br> measured at $\mathrm{I}_{\mathrm{R}}=1 \mathrm{~mA}$; see Fig. 7 | - | 4 | ns |
| $\mathrm{V}_{\mathrm{fr}}$ | forward recovery voltage | when switched from $\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}$; $\mathrm{t}_{\mathrm{r}}=20 \mathrm{~ns}$; see Fig. 8 | - | 1.75 | V |

## THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
| :--- | :--- | :--- | :---: | :---: |
| $\mathrm{R}_{\text {th } j \text {-tp }}$ | thermal resistance from junction to tie-point |  | 360 | $\mathrm{~K} / \mathrm{W}$ |
| $\mathrm{R}_{\text {th j-a }}$ | thermal resistance from junction to ambient | note 1 | 500 | $\mathrm{~K} / \mathrm{W}$ |

## Note

1. Device mounted on an FR4 printed-circuit board.

High-speed double diode

## GRAPHICAL DATA



## Device mounted on an FR4 printed-circuit board.

Fig. 2 Maximum permissible continuous forward current as a function of ambient temperature.

(1) $\mathrm{T}_{\mathrm{j}}=150^{\circ} \mathrm{C}$; typical values.
(2) $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; typical values.
(3) $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$; maximum values.

Fig. 3 Forward current as a function of forward voltage.


Fig. 4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.


Fig. 5 Reverse current as a function of junction temperature.

$\mathrm{f}=1 \mathrm{MHz} ; \mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$.
Fig. 6 Diode capacitance as a function of reverse voltage; typical values.

output signal
(1) $\mathrm{I}_{\mathrm{R}}=1 \mathrm{~mA}$.

Fig. 7 Reverse recovery voltage test circuit and waveforms.


Fig. 8 Forward recovery voltage test circuit and waveforms.

## PACKAGE OUTLINE



Fig. 9 SOT23.

## DEFINITIONS

## Data Sheet Status

| Objective specification | This data sheet contains target or goal specifications for product development. |
| :--- | :--- |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |

## Limiting values

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

## Application information

Where application information is given, it is advisory and does not form part of the specification.

## LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

